

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-310D0GVA

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
Top side :Gold pad.
Back side : SnAu Alloy.

3. Size :

- 3-1. Chip size : 10.0 mils x 10.0 mils (0.255 mm x 0.255 mm).
- 3-2. Chip thickness : 4.0 ± 1.0 mils (0.100 ± 0.025 mm).
- 3-3. Active area : 7.3 mils x 7.3 mils (0.185 mm x 0.185 mm).
- 3-4. Bonding pad : 7.7 mils x 7.7 mils (0.195 mm x 0.195 mm) .
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	$V_R=48V$ $E_e=0mW/cm^2$			100	nA
Zener Voltage	V_Z	$I_Z=5mA$ $E_e=0mW/cm^2$	50			V
Forward Voltage	V_f	$I_F=20mA$ $E_e=0mW/cm^2$			1.2	V

